TOSHIBA

TOSHIBA Photocoupler GaAs Ired & Photo-Triac

# **TLP763J**

Office Machine Household Use Equipment Triac Driver Solid State Relay

The TOSHIBA TLP763J consists of a GaAs infrared LED optically coupled to a zero voltage crossing turn-on photo-triac in a 6 lead plastic DIP.

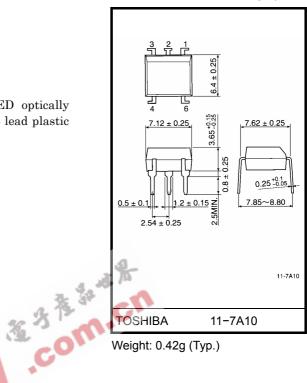
- Peak off-state voltage: 600 V (Min.) •
- Trigger LED current: 10 mA (Max.) •
- On-state current: 100 mA (Max.)
- Isolation voltage: 4000Vrms (Min.)
- UL recognized: UL1577, file No. E67349
  - BSI approved: BS EN60065: 2002, Certificate No. 8945
    - BS EN60950-1: 2002. Certificate No. 8946
- SEMKO approved: SS EN60065 (EN60065, 1993) SS EN60950 (EN60950, 1992)
  - SS EN60335 (EN60335, 1988)
  - Certificate No. 9522145
- Option (D4) type VDE approved: DIN EN 60747-5-2

Certificate No. 40009373

Maximum operating insulation voltage : 890 VPk Highest permissible over voltage : 6000 VPk

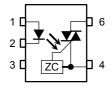
(Note) When an EN60747-5-2 approved type is needed, please designate the "option (D4)".

		7.62mm pich	10.16mm pich
		TLP763J type	TLP763JF type
•	Creepage distance	: 7.0mm (Min.)	8.0mm (Min.)
	Clearance	: 7.0mm (Min.)	8.0mm (Min.)
	Internal creepage path	: 4.0mm (Min.)	4.0mm (Min.)
	Insulation thickness	: 0.5mm (Min.)	0.5mm (Min.)



Weight: 0.42g (Typ.)

#### Pin configuration (top view)



- 1 : Anode
- 2 : Cathode
- 3 : N.C. 4 : Terminal 1
- 6: Terminal 2

Unit: mm

Absolute Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit	
LED	Forward current	lF	50	mA		
	Forward current derating (Ta ≥ 53	∆I <sub>F</sub> /°C	-0.7	mA/°C		
	Peak forward current (100 µs pulse, 100 pps)		I <sub>FP</sub>	1	А	
	Reverse voltage	V <sub>R</sub>	5	V		
	Junction temperature		Tj	125	°C	
	Off-state output terminal voltage		V <sub>DRM</sub>	600	V	
	On-state RMS current	Ta = 25°C		100	mA	
<u>ب</u>		Ta = 70°C	I <sub>T(RMS)</sub>	50	IIIA	
Detector	On–state current derating (Ta ≥ 25	ΔI <sub>T</sub> /°C	-1.1	mA/°C		
Det	Peak on-state current (100µs puls	I <sub>TP</sub>	2	А		
	Peak nonrepetitive surge current (PW = 10 ms, DC = 10%)	I <sub>TSM</sub>	1.2	А		
	Junction temperature	Тj	115	°C		
Storage temperature range			T <sub>stg</sub>	-55~125	°C	
Operating temperature range			T <sub>opr</sub>	-40~100	°C	
Lead soldering temperature (10s)			T <sub>sol</sub>	260	°C	
Isolation voltage (AC, 1 min., R.H.≤ 60%)			BVS	4000 Vrm		

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>AC</sub>	—	_	240	Vac
Forward current	١ <sub>F</sub>	15	20	25	mA
Peak on-state current	I <sub>TP</sub>	_	-	1	А
Operating temperature	T <sub>opr</sub>	-25		85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

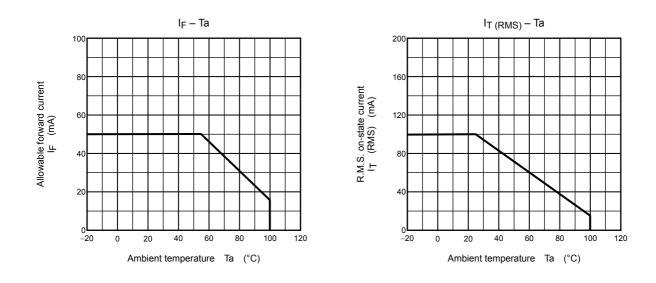
Electrical Characteristics (Ta = 25°C)

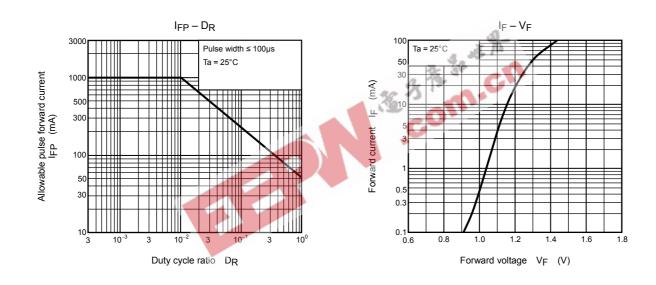
	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	VF	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	—	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	30	_	pF
	Peak off-state current	I <sub>DRM</sub>	V <sub>DRM</sub> = 600 V	_	10	1000	nA
	Peak on-state voltage	V <sub>TM</sub>	I <sub>TM</sub> = 100 mA		1.7	3.0	V
ctor	Holding current	Iн	_	-	0.6	_	mA
Detector	Critical rate of rise of off-state voltage	dv / dt	Vin = 240 V, Ta = 85°C	_	500	_	V/µs
	Critical rate of rise of commutating voltage	dv / dt (c)	Vin = 60Vrms , I <sub>T</sub> = 15 mA	_	0.2	—	V/µs

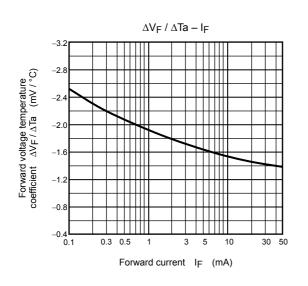
# **Coupled Electrical Characteristics (Ta = 25°C)**

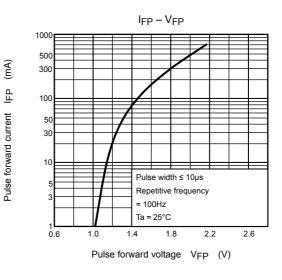
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I <sub>FT</sub>	V <sub>T</sub> = 6 V	—	—	10	mA
Inhibit voltage	VIH	I <sub>F</sub> = rated I <sub>FT</sub>	_	_	50	V
Leakage in inhibited state	IIН	I <sub>F</sub> = rated I <sub>FT</sub> V <sub>T</sub> = Rated V <sub>DRM</sub>	-	200	600	μA
Capacitance (input to output)	CS	V <sub>S</sub> = 0, f = 1 MHz	- ·	0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V	1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω
		AC, 1 minute	4000	—	_	Vrms
Isolation voltage	BVS	AC, 1 second, in oil	_	10000	-	VIIIIS
		DC, 1 minute, in oil	_	10000	_	V <sub>dc</sub>

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### **RESTRICTIONS ON PRODUCT USE**

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- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
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